

BUK6Y24-40P 40 V, P-channel Trench MOSFET 9 April 2020

Product data sheet

### 1. General description

P-channel enhancement mode MOSFET in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC-Q101 standard for use in high-performance automotive applications such as reverse battery protection.

### 2. Features and benefits

- High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating •
- Trench MOSFET technology •
- AEC-Q101 qualified

### 3. Applications

- Reverse battery protection
- Power management
- High-side load switch
- Motor drive

### 4. Quick reference data

| Table 1. Quid     | ck reference data                |  |     |     |     |     |      |
|-------------------|----------------------------------|--|-----|-----|-----|-----|------|
| Symbol            | Parameter                        | Conditions   |     | Min | Тур | Мах | Unit |
| V <sub>DS</sub>   | drain-source voltage             | T <sub>j</sub> = 25 °C   |     | -   | -   | -40 | V    |
| V <sub>GS</sub>   | gate-source voltage              |  | [1] | -20 | -   | 20  | V    |
| I <sub>D</sub>    | drain current                    | V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 25 °C                         |     | -   | -   | -39 | А    |
| P <sub>tot</sub>  | total power dissipation          | T <sub>mb</sub> = 25 °C  |     | -   | -   | 66  | W    |
| Static chara      | octeristics                      |  | •   |     |     |     |      |
| R <sub>DSon</sub> | drain-source on-state resistance | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C |     | -   | 19  | 24  | mΩ   |

[1]  $V_{GS}$  = -20 V/+5 V according AEC-Q101 at T<sub>j</sub> = 175 °C;  $V_{GS}$  = -20 V/+20 V according AEC-Q101 at T<sub>j</sub> = 150 °C

# nexperia

# 5. Pinning information

| Table 2 | . Pinning info | rmation                           |                                 |                |
|---------|----------------|-----------------------------------|---------------------------------|----------------|
| Pin     | Symbol         | Description                       | Simplified outline              | Graphic symbol |
| 1       | S              | source                            | mb                              | D              |
| 2       | S              | source                            |                                 |                |
| 3       | S              | source                            | a                               | G              |
| 4       | G              | gate                              |                                 | s              |
| mb      | D              | mounting base; connected to drain | LFPAK56; Power-<br>SO8 (SOT669) | 017aaa094      |

### 6. Ordering information

| Table 3. Ordering information       Type number     Package |                       |  |         |  |  |  |  |
|---|-----------------------|--|---------|--|--|--|--|
| Type number   | Name                  | Description  | Version |  |  |  |  |
| BUK6Y24-40P   | LFPAK56;<br>Power-SO8 | plastic, single-ended surface-mounted package; 4 terminals | SOT669  |  |  |  |  |

# 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BUK6Y24-40P            | 6Y2440P      |

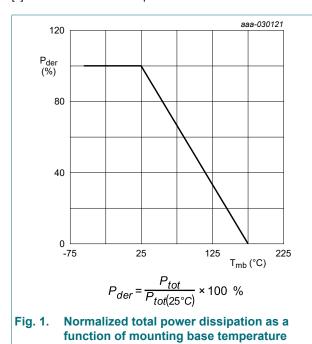
### 8. Limiting values

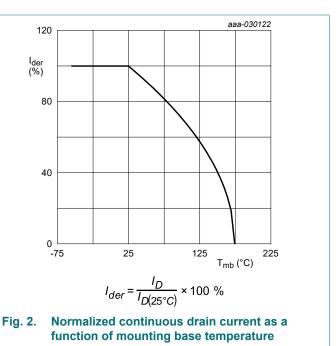
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

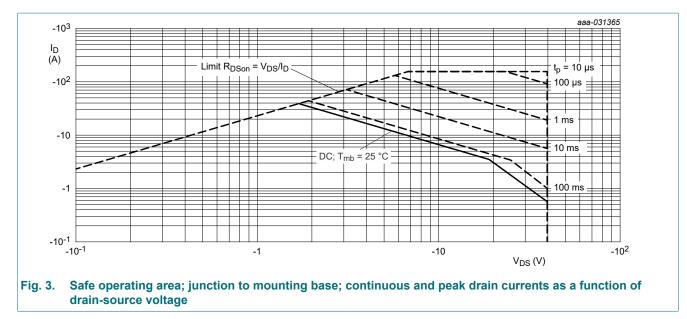
| Symbol               | Parameter  | Conditions   |     | Min | Max  | Unit |
|----------------------|--|--|-----|-----|------|------|
| V <sub>DS</sub>      | drain-source voltage                             | T <sub>j</sub> = 25 °C   |     | -   | -40  | V    |
| V <sub>GS</sub>      | gate-source voltage                              | -  | [1] | -20 | 20   | V    |
| ID                   | drain current                                    | V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 25 °C   |     | -   | -39  | А    |
|                      |  | V <sub>GS</sub> = -10 V; T <sub>mb</sub> = 100 °C  |     | -   | -27  | А    |
| I <sub>DM</sub>      | peak drain current                               | single pulse; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$                           |     | -   | -155 | А    |
| P <sub>tot</sub>     | total power dissipation                          | T <sub>mb</sub> = 25 °C  |     | -   | 66   | W    |
| Tj                   | junction temperature                             |  |     | -55 | 175  | °C   |
| T <sub>amb</sub>     | ambient temperature                              |  |     | -55 | 175  | °C   |
| T <sub>stg</sub>     | storage temperature                              |  |     | -65 | 175  | °C   |
| Source-drai          | in diode   |  |     |     |      |      |
| Is                   | source current                                   | T <sub>mb</sub> = 25 °C  |     | -   | -39  | А    |
| I <sub>SM</sub>      | peak source current                              | single pulse; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$                           |     | -   | -155 | А    |
| ESD maxim            | num rating                                       |  |     |     |      |      |
| V <sub>ESD</sub>     | electrostatic discharge voltage                  | НВМ  | [2] | -   | 500  | V    |
| Avalanche            | ruggedness                                       | 1  |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = -4.6 A; DUT in<br>v avalanche (unclamped) |     | -   | 54   | mJ   |

[1]  $V_{GS}$  = -20 V/+5 V according AEC-Q101 at T<sub>j</sub> = 175 °C;  $V_{GS}$  = -20 V/+20 V according AEC-Q101 at T<sub>j</sub> = 150 °C [2] Measured between all pins.





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### 9. Thermal characteristics

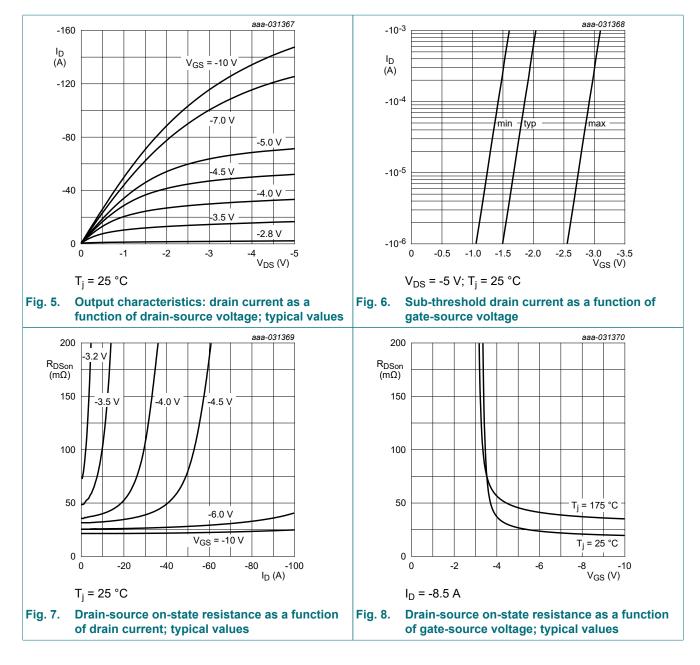
| Symbol                | Parameter   | Conditions | Min | Тур | Мах | Unit |
|-----------------------|---|------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance from junction to mounting base |            | -   | 1.8 | 2.3 | K/W  |



### **10. Characteristics**

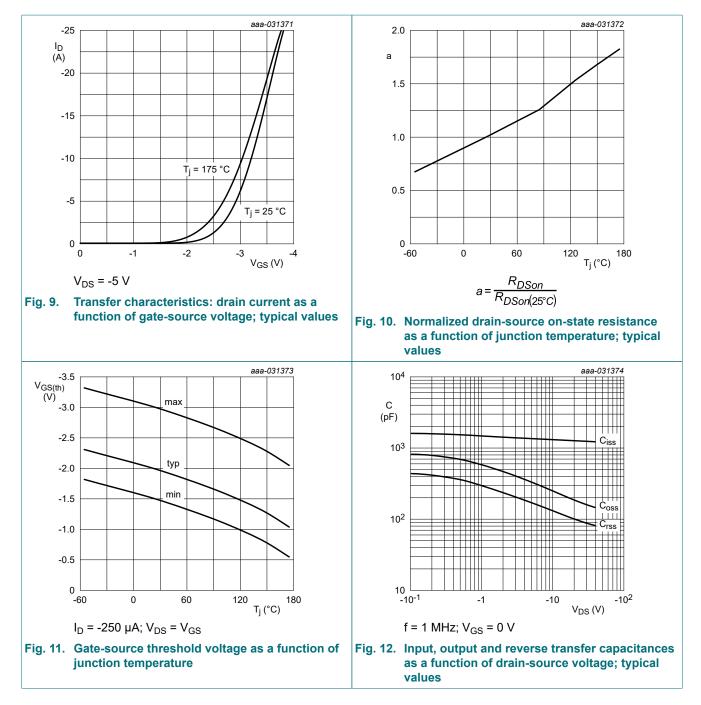
| Symbol                | Parameter                         | Conditions  | Min  | Тур  | Max  | Unit |
|-----------------------|-----------------------------------|---|------|------|------|------|
| Static chara          | cteristics                        |   |      |      |      |      |
| V <sub>(BR)DSS</sub>  | drain-source<br>breakdown voltage | I <sub>D</sub> = -250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C             | -40  | -    | -    | V    |
| V <sub>GSth</sub>     | gate-source threshold voltage     | I <sub>D</sub> = -250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C | -1.5 | -2   | -3   | V    |
| I <sub>DSS</sub> drai | drain leakage current             | V <sub>DS</sub> = -40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -    | -    | -1   | μA   |
|                       |                                   | V <sub>DS</sub> = -40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C             | -    | -    | -10  | μA   |
| I <sub>GSS</sub>      | gate leakage current              | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C              | -    | -    | -100 | nA   |
|                       |                                   | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -    | -    | 100  | nA   |
| R <sub>DSon</sub>     | drain-source on-state             | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 25 °C            | -    | 19   | 24   | mΩ   |
|                       | resistance                        | V <sub>GS</sub> = -10 V; I <sub>D</sub> = -8.2 A; T <sub>j</sub> = 175 °C           | -    | 35   | 44   | mΩ   |
|                       |                                   | V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -5.6 A; T <sub>j</sub> = 25 °C           | -    | 30   | 50   | mΩ   |
| 9 <sub>fs</sub>       | forward<br>transconductance       | V <sub>DS</sub> = -10 V; I <sub>D</sub> = -4 A; T <sub>j</sub> = 25 °C              | -    | 14   | -    | S    |
| R <sub>G</sub>        | gate resistance                   | f = 1 MHz   | -    | 11   | -    | Ω    |
| Dynamic ch            | aracteristics                     |   |      |      |      |      |
| Q <sub>G(tot)</sub>   | total gate charge                 | V <sub>DS</sub> = -20 V; I <sub>D</sub> = -8.2 A; V <sub>GS</sub> = -10 V;          | -    | 23   | 35   | nC   |
| Q <sub>GS</sub>       | gate-source charge                | T <sub>j</sub> = 25 °C  | -    | 4    | -    | nC   |
| Q <sub>GD</sub>       | gate-drain charge                 |   | -    | 5    | -    | nC   |
| C <sub>iss</sub>      | input capacitance                 | V <sub>DS</sub> = -20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;                          | -    | 1250 | -    | pF   |
| C <sub>oss</sub>      | output capacitance                | T <sub>j</sub> = 25 °C  | -    | 184  | -    | pF   |
| C <sub>rss</sub>      | reverse transfer capacitance      |   | -    | 100  | -    | pF   |
| t <sub>d(on)</sub>    | turn-on delay time                | $V_{DS}$ = -20 V; $I_D$ = -8.2 A; $V_{GS}$ = -10 V;                                 | -    | 7    | -    | ns   |
| t <sub>r</sub>        | rise time                         | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$  | -    | 25   | -    | ns   |
| t <sub>d(off)</sub>   | turn-off delay time               |   | -    | 50   | -    | ns   |
| t <sub>f</sub>        | fall time                         |   | -    | 450  | -    | ns   |
| Source-drai           | n diode                           |   |      |      |      |      |
| V <sub>SD</sub>       | source-drain voltage              | I <sub>S</sub> = -39 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C               | -    | -0.7 | -1.2 | V    |
| t <sub>rr</sub>       | reverse recovery time             | I <sub>S</sub> = -39 A; dI <sub>S</sub> /dt = 100 A/μs;                             | -    | 21   | -    | ns   |
| Q <sub>r</sub>        | recovered charge                  | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = -20 V; T <sub>j</sub> = 25 °C            | -    | 18   | -    | nC   |

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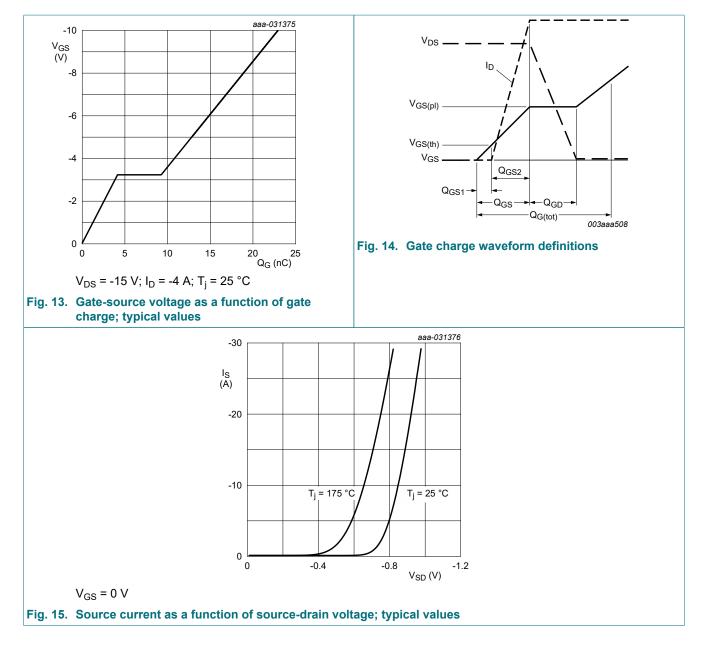


**Product data sheet** 

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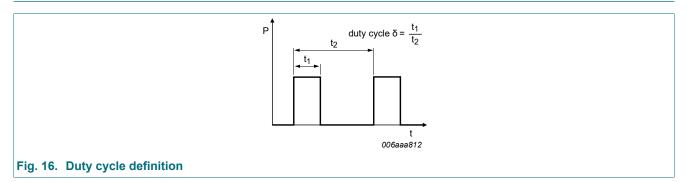


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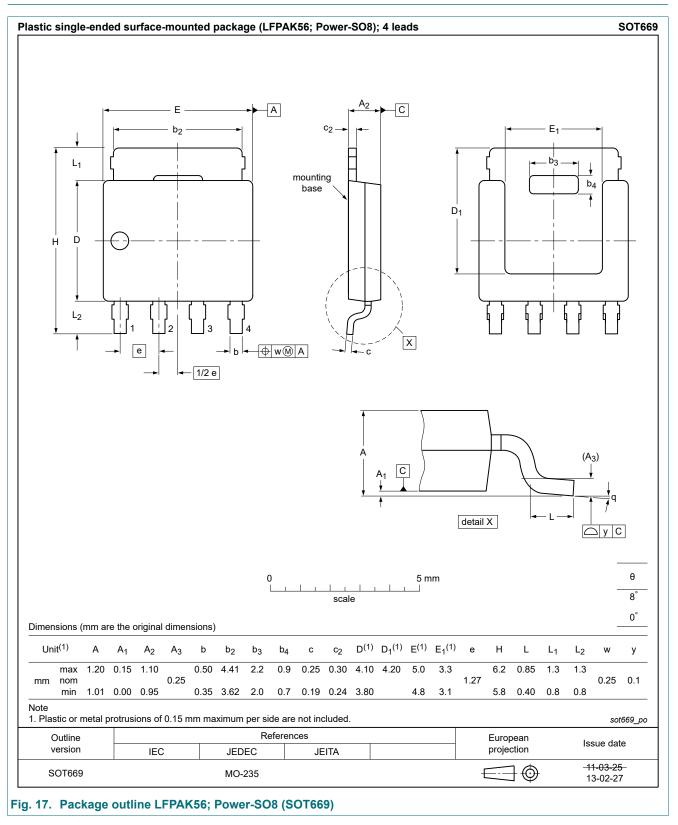
### **11. Test information**



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



# 13. Revision history

| Table 8. Revision history |              |                    |               |            |  |  |
|---------------------------|--------------|--------------------|---------------|------------|--|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |  |
| BUK6Y24-40P v.1           | 20200409     | Product data sheet | -             | -          |  |  |

**Product data sheet** 

### 14. Legal information

#### Data sheet status

| Document status [1][2]            | Product<br>status [3] | Definition  |
|-----------------------------------|-----------------------|---|
| Objective [short]<br>data sheet   | Development           | This document contains data from<br>the objective specification for<br>product development. |
| Preliminary [short]<br>data sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product [short]<br>data sheet     | Production            | This document contains the product specification.   |

 Please consult the most recently issued document before initiating or completing a design.

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